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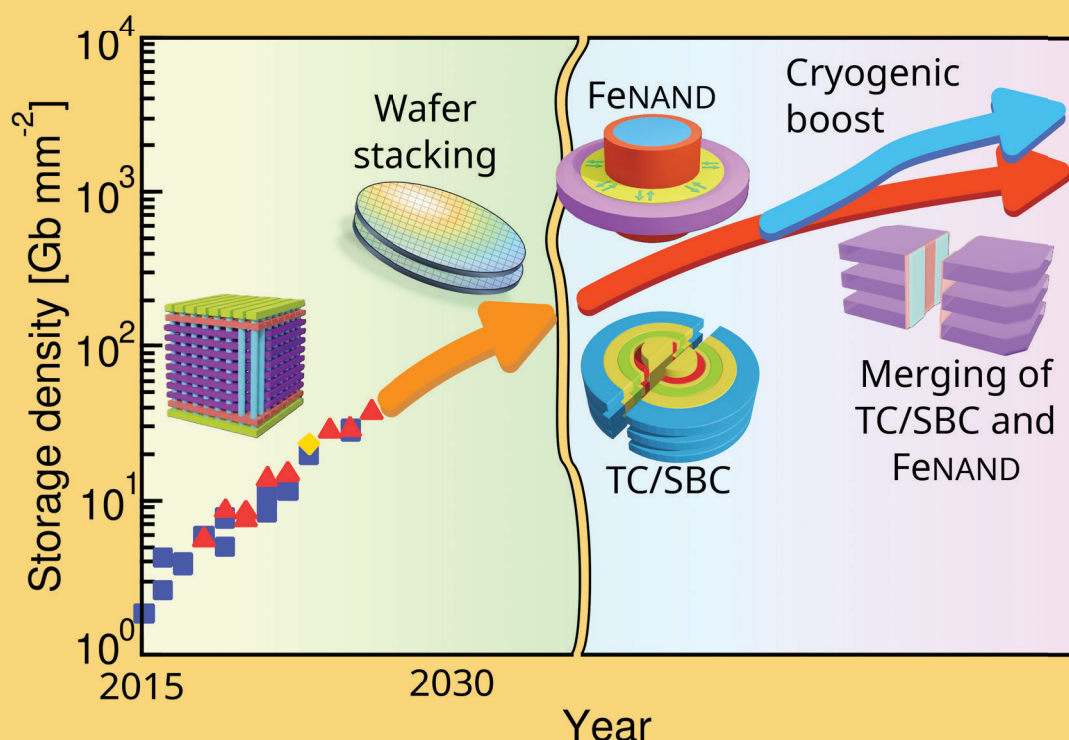
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Invited Paper: Research Challenges in 3-D NAND Flash



Editor's Highlights:

- Ge/GeSn Quantum Well MOSFETs for Cryogenic Applications (Silicon and Column IV Semiconductor Devices)
- Semi-On State Hole Generation in GaN HEMTs: Experimental Evidence and TCAD Modeling (Compound Semiconductor Devices)
- Buried V-Pit Templates for 20.3% Peak EQE at 640 nm in InGaN Red LEDs (Optoelectronics, Display, Imaging)
- Selector-Free Ternary Content-Addressable Memory on 3-D Stacked Complementary FeCAP (Emerging Technologies and Devices)



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